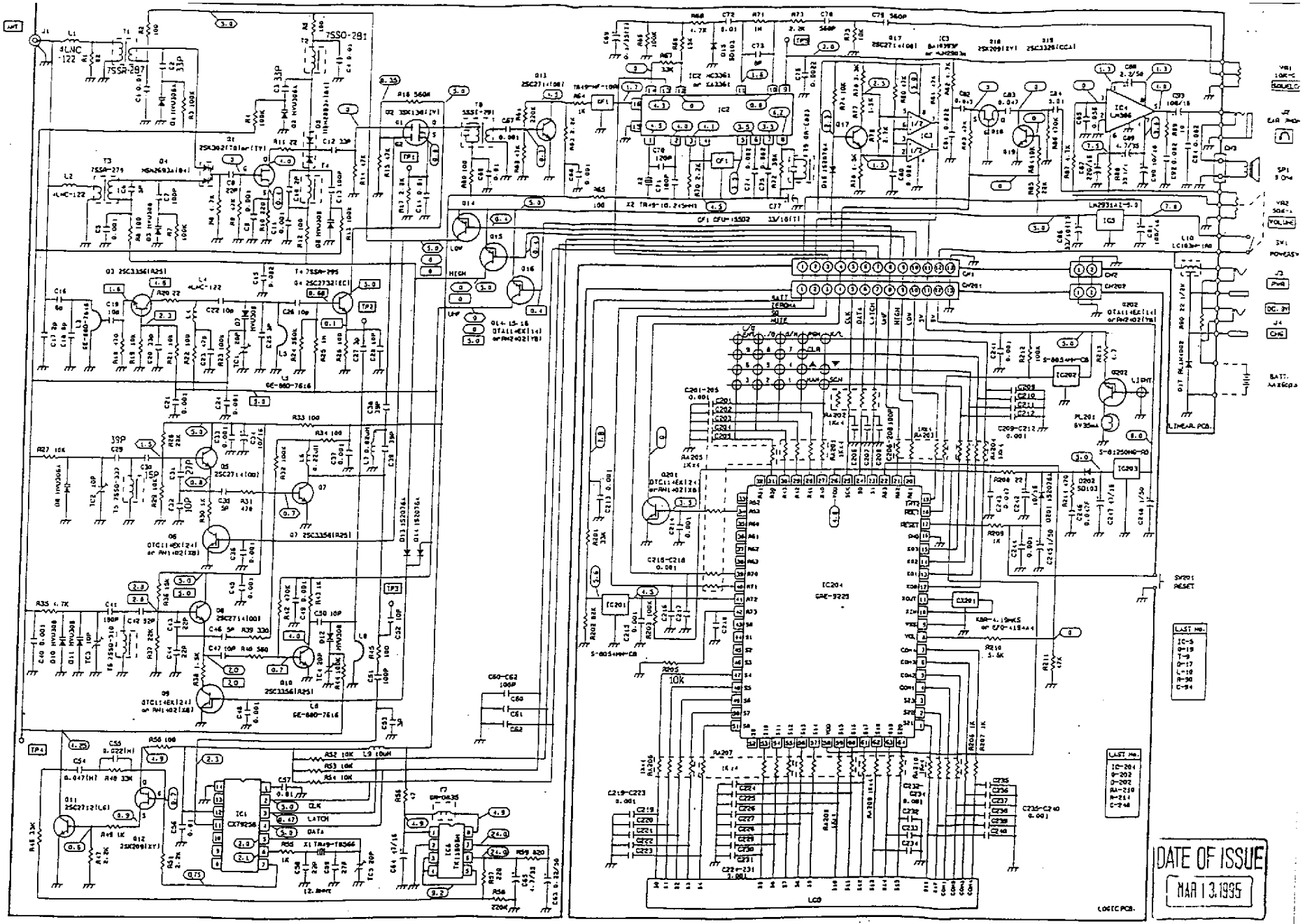

NOTES

1. RESISTANCE VALUES IN OHMS (K=1000, M=1000000)
2. CAPACITANCE VALUES IN uF (P=uuF)
3. (T)=TANTALUM CAPACITOR
4. (N)=MYLAR CAPACITOR
5. NO SUFFERED CERAMIC or CHIP CAPACITOR
6. ⬭ THIS SYMBOL DENOTES DC VOLTAGE WITH DC VOLTMETER (100K ohm/V) UNDER FOLLOWING CONDITIONS.
   CH1 HIGH BAND AT 150MHz, MANUAL OPERATION.
   VOLUME AT MINIMUM AND SQUELCH CCW
7. ⬭ THIS SYMBOL DENOTES VOLTAGES FOR LOW BAND OPERATION
8. ▭ THIS SYMBOL DENOTES VOLTAGES FOR UHF BAND OPERATION

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